Integrated Device Technology, Inc.

FAST CMOS OCTAL REGISTERED TRANSCEIVER

PRELIMINARY
IDT 54/74FCT543
IDT 54/74FCT543A

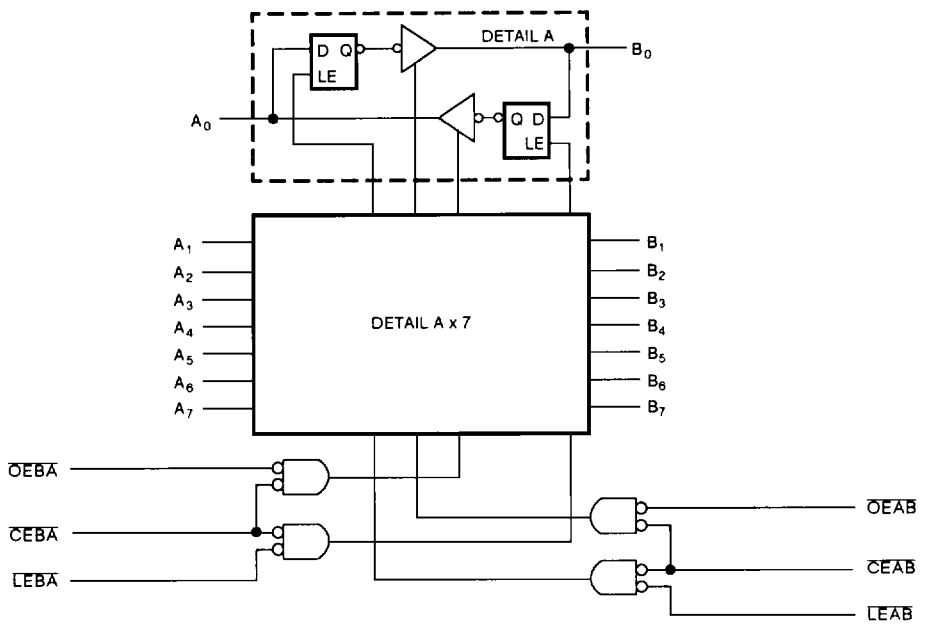
FEATURES:

- IDT54/74FCT543 equivalent to FAST™ speed;
  IDT54/74FCT543A is 25% faster than FAST™
- Equivalent to FAST™ output drive over full temperature and voltage supply extremes
- I_{OL} = 64mA (commercial), 48mA (military)
- 8-bit octal latched transceiver
- Separate controls for data flow in each direction
- Back-to-back latches for storage
- CMOS power levels (5μW typ. static)
- Substantially lower input current levels than FAST™ (5μA max.)
- TTL input and output level compatible
- CMOS output level compatible
- Product available in Radiation Tolerant and Enhanced versions
- Military product compliant to MIL-STD-883, Class B

DESCRIPTION:

The IDT54/74FCT543 and IDT54/74FCT543A are non-inverting octal transceivers built using advanced CEMOS™, a dual metal CMOS technology. These devices contain two sets of eight D-type latches with separate input and output controls for each set. For data flow from A to B, for example, the A-to-B Enable ($\overline{CEAB}$) input must be LOW in order to enter data from A_0-A_7 or to take data from B_0-B_7, as indicated in the Truth Table. With $\overline{CEAB}$ LOW, a LOW signal on the A-to-B Latch Enable ($\overline{LEAB}$) input makes the A-to-B latches transparent; a subsequent LOW-to-HIGH transition of the $\overline{LEAB}$ signal puts the A latches in the storage mode and their outputs no longer change with the A inputs. With $\overline{CEAB}$ and $\overline{OEAB}$ both LOW, the 3-state B output buffers are active and reflect the data present at the output of the A latches. Control of data from B to A is similar, but uses the $\overline{CEBA}$, $\overline{LEBA}$ and $\overline{OEBA}$ inputs.

FUNCTIONAL BLOCK DIAGRAM



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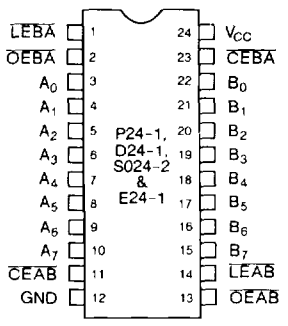
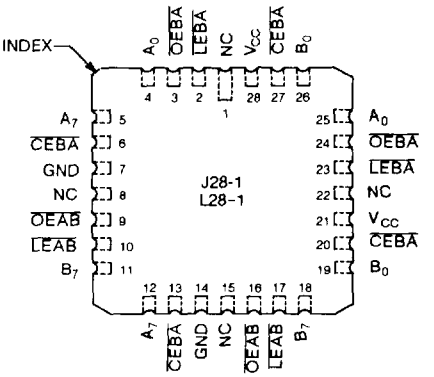
FAST is a trademark of Fairchild Semiconductor Co.

PIN CONFIGURATIONS

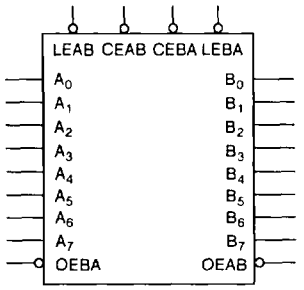


DIP/SOIC/CERPACK
TOP VIEW



LCC/PLCC
TOP VIEW

LOGIC SYMBOL



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TRUTH TABLE For A-TO-B (Symmetric with B-TO-A)

INPUTS			LATCH STATUS	OUTPUT BUFFERS
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A-TO-B	B_0-B_7
H	X	X	Storing	High Z
X	H	–	Storing	–
X	–	H	–	High Z
L	L	L	Transparent	Current A Inputs
L	H	L	Storing	Previous* A Inputs

* Before $\overline{LEAB}$ LOW-to-HIGH Transition

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

A-to-B data flow shown: B-to-A flow control is the same, except using $\overline{CEBA}$, $\overline{LEBA}$ and $\overline{OEBA}$

PIN DESCRIPTIONS

PIN NAMES	DESCRIPTION
$\overline{OEAB}$	A-to-B Output Enable Input (Active LOW)
$\overline{OEBA}$	B-to-A Output Enable Input (Active LOW)
$\overline{CEAB}$	A-to-B Enable Input (Active LOW)
$\overline{CEBA}$	B-to-A Enable Input (Active LOW)
$\overline{LEAB}$	A-to-B Latch Enable Input (Active LOW)
$\overline{LEBA}$	B-to-A Latch Enable Input (Active LOW)
A_0-A_7	A-to-B Data Inputs or B-to-A 3-State Outputs
B_0-B_7	B-to-A Data Inputs or A-to-B 3-State Outputs

ABSOLUTE MAXIMUM RATINGS [1]

SYMBOL	RATING	COMMERCIAL	MILITARY	UNIT
V_{TERM} [2]	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
V_{TERM} [3]	Terminal Voltage with Respect to GND	-0.5 to V_{CC}	-0.5 to V_{CC}	V
T_A	Operating Temperature	0 to +70	-55 to +125	°C
T_{BIAS}	Temperature Under Bias	-55 to +125	-65 to +135	°C
T_{STG}	Storage Temperature	-55 to +125	-65 to +150	°C
P_T	Power Dissipation	0.5	0.5	W
I_{OUT}	DC Output Current	100	100	mA

NOTES:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. Input and V_{CC} terminals only.
3. Output and I/O terminals only.

CAPACITANCE (T_A = +25°C, f = 1.0MHz)

SYMBOL	PARAMETER[1]	CONDITIONS	TYP.	MAX.	UNIT
C_{IN}	Input Capacitance	V_{IN} = 0V	6	10	pF
$C_{I/O}$	I/O Capacitance	V_{OUT} = 0V	8	12	pF

NOTE:

1. This parameter is guaranteed by characterization data and not tested.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:
V_{LC} = 0.2V; V_{HC} = V_{CC} - 0.2V
Commercial: T_A = 0°C to +70°C; V_{CC} = 5.0V±5%
Military: T_A = -55°C to +125°C; V_{CC} = 5.0V±10%

SYMBOL	PARAMETER	TEST CONDITIONS[1]		MIN.	TYP.[2]	MAX.	UNIT
V_{IH}	Input HIGH Level	Guaranteed Logic High Level		2.0	–	–	V
V_{IL}	Input LOW Level	Guaranteed Logic Low Level		–	–	0.8	V
I_{IH}	Input HIGH Current (Except I/O pins)	V_{CC} = Max.	V_I = V_{CC}	–	–	5	µA
			V_I = 2.7V	–	–	5[4]	
I_{IL}	Input LOW Current (Except I/O pins)		V_I = 0.5V	–	–	-5[4]	
			V_I = GND	–	–	-5	
I_{IH}	Input HIGH Currents (I/O pins only)	V_{CC} = Max.	V_I = V_{CC}	–	–	15	µA
			V_I = 2.7V	–	–	15[4]	
I_{IL}	Input LOW Currents (I/O pins only)		V_I = 0.5V	–	–	-15[4]	
			V_I = GND	–	–	-15	
V_{IK}	Clamp Diode Voltage	V_{CC} = Min., I_N = -18mA		–	-0.7	-1.2	V
I_{OS}	Short Circuit Current	V_{CC} = Max.[3], V_O = GND		-60	-120	–	mA
V_{OH}	Output HIGH Voltage	V_{CC} = 3V, V_{IN} = V_{LC} or V_{HC}, I_{OH} = -32 µA		V_{HC}	V_{CC}	–	V
		V_{CC} = Min. V_{IN} = V_{IH} or V_{IL}	I_{OH} = -300µA	V_{HC}	V_{CC}	–	
			I_{OH} = -12mA MIL.	2.4	4.3	–	
			I_{OH} = -15mA COM'L.	2.4	4.3	–	
V_{OL}	Output LOW Voltage	V_{CC} = 3V, V_{IN} = V_{LC} or V_{HC}, I_{OL} = 300µA		–	GND	V_{LC}	V
		V_{CC} = Min. V_{IN} = V_{IH} or V_{IL}	I_{OL} = 300µA	–	GND	V_{LC}	
			I_{OL} = 48mA MIL.[5]	–	0.3	0.55	
			I_{OL} = 64mA COM'L.[5]	–	0.3	0.55	

NOTES:

1. For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at V_{CC} = 5.0V, +25°C ambient and maximum loading.
3. Not more than one output should be shorted at one time. Duration of the short circuit test should not exceed one second.
4. This parameter is guaranteed but not tested.
5. These are maximum I_{OL} values per output, for 8 outputs turned on simultaneously. Total maximum I_{OL} (all outputs) is 512mA for commercial and 384mA for military. Derate I_{OL} for number of outputs exceeding 8 turned on simultaneously.

POWER SUPPLY CHARACTERISTICS

V_{LC} = 0.2V; V_{HC} = V_{CC} - 0.2V

SYMBOL	PARAMETER	TEST CONDITIONS[1]		MIN.	TYP.[2]	MAX.	UNIT
I_{CC}	Quiescent Power Supply Current	V_{CC} = Max. $V_{IN} \geq V_{HC}$; $V_{IN} \leq V_{LC}$ $f_{CP} = f_i = 0$		–	0.001	1.5	mA
ΔI_{CC}	Quiescent Power Supply Current TTL Inputs HIGH	V_{CC} = Max. V_{IN} = 3.4V[3]		–	0.5	2.0	mA
I_{CCD}	Dynamic Power Supply Current[4]	V_{CC} = Max. Outputs Open $\overline{CEAB}$ & $\overline{OEAB}$ = GND $\overline{CEBA}$ = V_{CC} One Input Toggling 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$	–	0.15	0.25	mA/ MHz
I_C	Total Power Supply Current[6]	V_{CC} = Max. Outputs Open f_{CP} = 10MHz 50% Duty Cycle $\overline{CEAB}$ & $\overline{OEAB}$ = GND $\overline{CEBA}$ = V_{CC} f_{CP} = $\overline{LEAB}$ = 10MHz One Bit Toggling at f_i = 5MHz 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$ (FCT)	–	1.5	4.0	mA
			V_{IN} = 3.4V or V_{IN} = GND	–	2.0	6.0	
		V_{CC} = Max. Outputs Open f_{CP} = 10MHz 50% Duty Cycle $\overline{CEAB}$ & $\overline{OEAB}$ = GND $\overline{CEBA}$ = V_{CC} f_{CP} = $\overline{LEAB}$ = 10MHz Eight Bits Toggling at f_i = 5MHz 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$ (FCT)	–	3.75	12.75[5]	
			V_{IN} = 3.4V or V_{IN} = GND	–	6.0	21.75[5]	

NOTES:

1. For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at V_{CC} = 5.0V, +25°C ambient and maximum loading.
3. Per TTL driven input (V_{IN} = 3.4V); all other inputs at V_{CC} or GND.
4. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
5. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.
6. $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$
   $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_{CP}/2 + f_i N_i)$
   I_{CC} = Quiescent Current
   ΔI_{CC} = Power Supply Current for a TTL High Input (V_{IN} = 3.4V)
   D_H = Duty Cycle for TTL Inputs High
   N_T = Number of TTL Inputs at D_H
   I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)
   f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)
   f_i = Input Frequency
   N_i = Number of Inputs at f_i
   All currents are in milliamps and all frequencies are in megahertz.

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SWITCHING CHARACTERISTICS OVER OPERATING RANGE

SYMBOL	PARAMETER	CONDITION[1]	IDT54/74FCT543					IDT54/74FCT543A					UNIT
			TYP.[3]	COM'L.		MIL.		TYP.[3]	COM'L.		MIL.		
				MIN.[2]	MAX.	MIN.[2]	MAX.		MIN.[2]	MAX.	MIN.[2]	MAX.	
t_{PLH} t_{PHL}	Propagation Delay Transparent Mode A_n to B_n or B_n to A_n	C_L = 50pF R_L = 500Ω	5.0	2.5	8.5	2.5	10.0	–	2.5	6.5	2.5	7.5	ns
t_{PLH} t_{PHL}	Propagation Delay $\overline{LEBA}$ to A_n, $\overline{LEAB}$ to B_n		8.5	2.5	12.5	2.5	14.0	–	2.5	8	2.5	9	ns
t_{PZH} t_{PZL}	Output Enable Time $\overline{OEBA}$ or $\overline{OEAB}$ to A_n or B_n $\overline{CEBA}$ or $\overline{CEAB}$ to A_n or B_n		7.0	2.0	12.0	2.0	14.0	–	2	9	2	10	ns
t_{PHZ} t_{PLZ}	Output Disable Time $\overline{OEBA}$ or $\overline{OEAB}$ to A_n or B_n $\overline{CEBA}$ or $\overline{CEAB}$ to A_n or B_n		5.5	2.0	9.0	2.0	13.0	–	2	7.5	2	8.5	ns
t_{SU}	Set-up Time, HIGH or LOW A_n or B_n to $\overline{LEBA}$ or $\overline{LEAB}$		–	3.0	–	3.0	–	–	2	–	2	–	ns
t_H	Hold Time, HIGH or LOW A_n or B_n to $\overline{LEBA}$ or $\overline{LEAB}$		–	2.0	–	2.0	–	–	2	–	2	–	ns

NOTES:

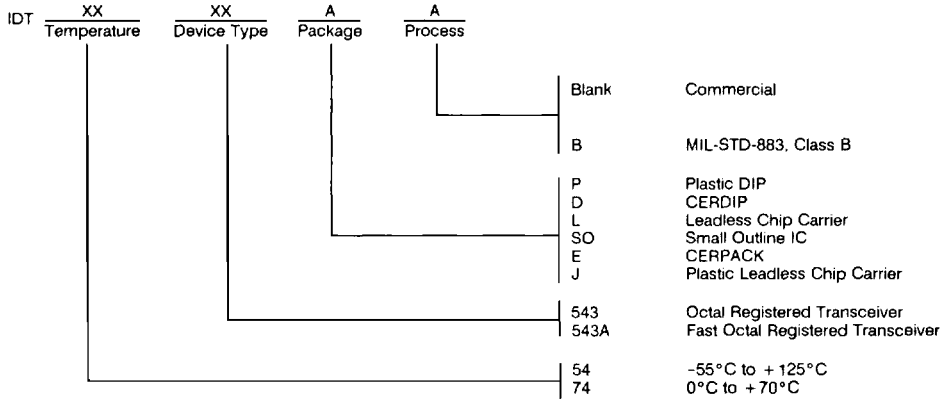
1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. Typical values are at V_{CC} = 5.0V, +25°C ambient and maximum loading.

CMOS TESTING CONSIDERATIONS

Special test board considerations must be taken into account when applying high-speed CMOS products to the automatic test environment. Large output currents are being switched in very short periods and proper testing demands that test set-ups have minimized inductance and guaranteed zero voltage grounds. The techniques listed below will assist the user in obtaining accurate testing results:

1) All input pins should be connected to a voltage potential during testing. If left floating, the device may oscillate, causing improper device operation and possible latchup.
2) Placement and value of decoupling capacitors is critical. Each physical set-up has different electrical characteristics and it is recommended that various decoupling capacitor sizes be experimented with. Capacitors should be positioned using the minimum lead lengths. They should also be distributed to decouple power supply lines and be placed as close as possible to the DUT power pins.
3) Device grounding is extremely critical for proper device testing. The use of multi-layer performance boards with radial decoupling between power and ground planes is necessary. The ground plane must be sustained from the performance board to the DUT interface board and wiring unused interconnect pins to the ground plane is recommended. Heavy gauge stranded wire should be used for power wiring, with twisted pairs being recommended for minimized inductance.
4) To guarantee data sheet compliance, the input thresholds should be tested per input pin in a static environment. To allow for testing and hardware-induced noise, it may be necessary to use $V_{IL} \leq 0V$ and $V_{IH} \geq 3V$ for ATE testing purposes.

ORDERING INFORMATION



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